

Semiconductor devices: Diodes, Thyristors, Optoelectronic devices

Текст для поиска...

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Advertising

Popular Materials

- 2D904A-1, 2D904B-1, 2D904B-1, 2D904G-1, 2D904D-1, 2D904E-1; CD904A-1, CD904B-1, CD904B-1, CD904G-1, CD904D-1, CD904E-1
- CC402A, KC402B, KC402B, KC402G, KC402D, KC402E, KC402Zh, KC402I, KC403A, KC403B, KC403B, KC403G, KC403D, KC403E, KC403I, KC404A, CC404B, CC404B, CC404B, CC404G, CC404D, CC404E, CC404I, CC4I, CC405A, CC405B, CC401B, CC405G, CC405D, CC405D, CC405E, CC405I, CC40405I, CC404B, CC404B, CC404B, CC403D
- 3I202A, 3I202B, 3I202B, 3I202G, 3I202D, 3I202E, 3I202Zh, 3I202I, 3I202K
- 3I203A, 3I203B, 3I203G, 3I203D, 2I203Zh, 3I203I
- Alphabetical digital pointer
- Classification and symbol system

Our projects:

- Semiconductor Devices
- Household acoustics of the USSR
- Speaker heads
- Construction workbook
- Zhitya Tvarin Svetu
- Roadside in the Crimea to the World

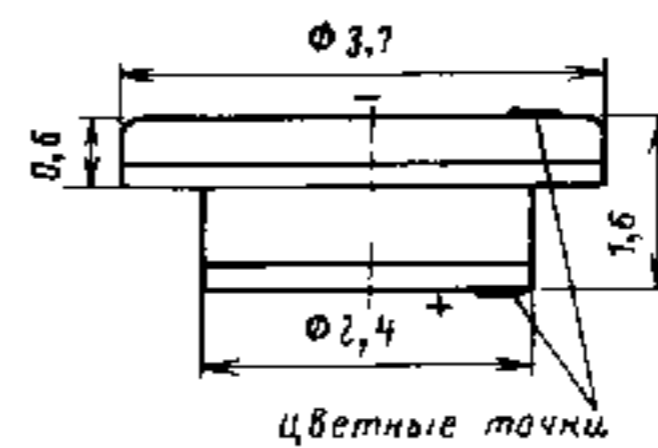
1I308A, 1I308B, 1I308B, 1I308G, 1I308D, 1I308E, 1I308Zh, 1I308I, 1I308K

1I308A, 1I308B, 1I308B, 1I308G, 1I308D, 1I308E, 1I308Zh, 1I308I, 1I308K

German tunnel mesaplanar diodes. Designed to work in subnanosecond switch devices.

Available in a metal-ceramic housing with rigid pins. The diode type is indicated on the label. Diodes are marked with the Color Code: **1I308A** - green and black dots, **1I308B** - green and white dots, **1I308B** - red and black dots, **1I308G** - two red dots, **1I308D** - red and white dots, **1I308E** - white and black dots, **1I308G** - two white dots, **1I308I** - blue and black dots, **1I308K** - blue and white dots. The negative pin has a larger diameter.

The weight of the diode is not more than 0.1 g.



Electrical parameters

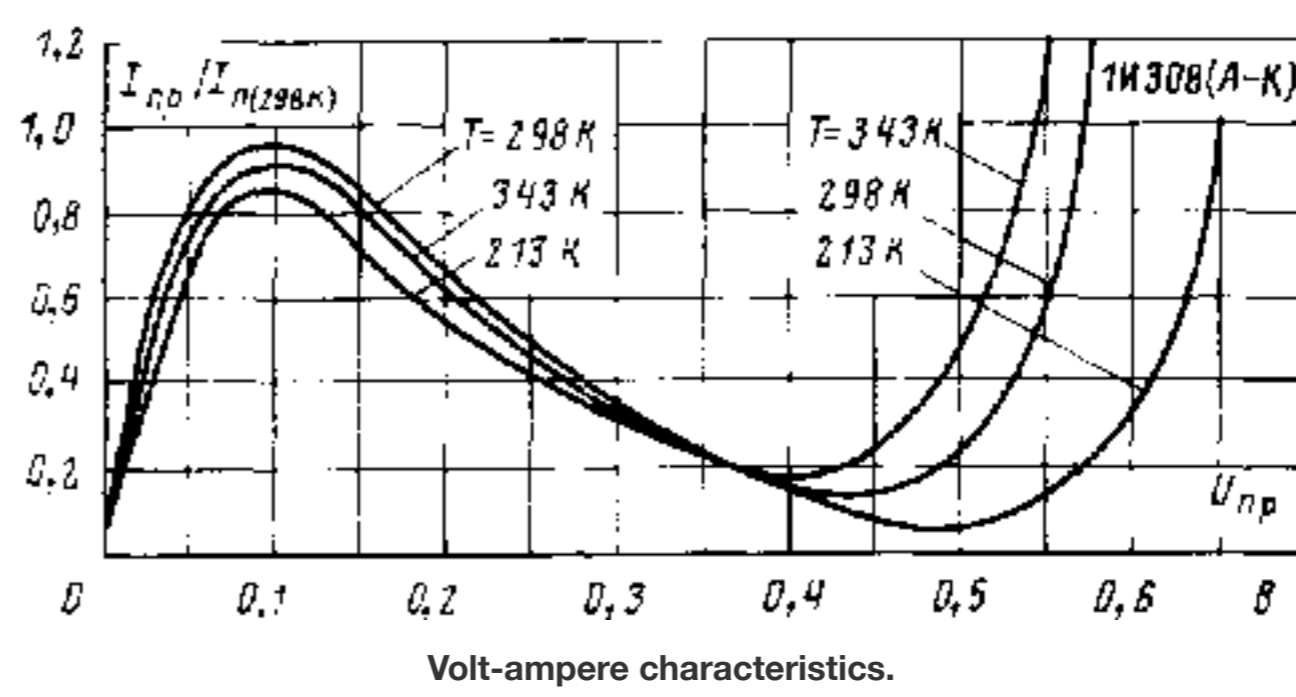
Peak current:	
1I308A, 1I308B	4.5 to 5.5 mA
1I308B, 1I308G, 1I308D	9.0 to 11 mA
1I308E, 1I308Zh	From 18 to 22 mA
1I308I, 1I308K	From 45 to 55 mA
The ratio of peak current to depression current, not less than:	
at 298 K	5
at 213 and 343 K	4
Total diode capacity at the point of minimum volt-ampere characteristic at f=1...10 MHz:	
1I308A, 1I308G	1.5 to 5 pF
1I308B	0.7 to 2 pF
1I308B	4.0 to 10 pF
1I308D	0.8 to 2 pF
1I308E	From 3.0 to 15 pF
1I308Zh	From 1.0 to 4 pF
1I308I	From 5.0 to 20 pF
1I308K	2.3 to 8 pF
Peak voltage*:	
1I308A	70 to 100 mV
1I308B	70 to 110 mV
1I308B	From 60 to 110 mV
1I308G	From 60 to 120 mV
1I308D	70 to 130 mV
1I308E	80 to 140 mV
1I308Zh	85 to 160 mV
1I308I	From 100 to 150 mV
1I308K	100 to 180 mV
Depression voltage*	350 to 480 mV
Solution voltage*	From 510 to 630 mV
Temperature coefficient of peak current* at temperature, no worse than:	
from 273 to 343 K	-0.35%/K
from 213 to 343 K	-0.25%/K
Thermal current coefficient* at temperatures from 213 to 343 K, not more than	0.6%/K
Temperature coefficient of solution voltage*	0.5 to 1.5 mV/K
Case capacity*	0.42 to 0.58 pF
Diode inductance*	0.2 to 0.35 nGn

Maximum operational data

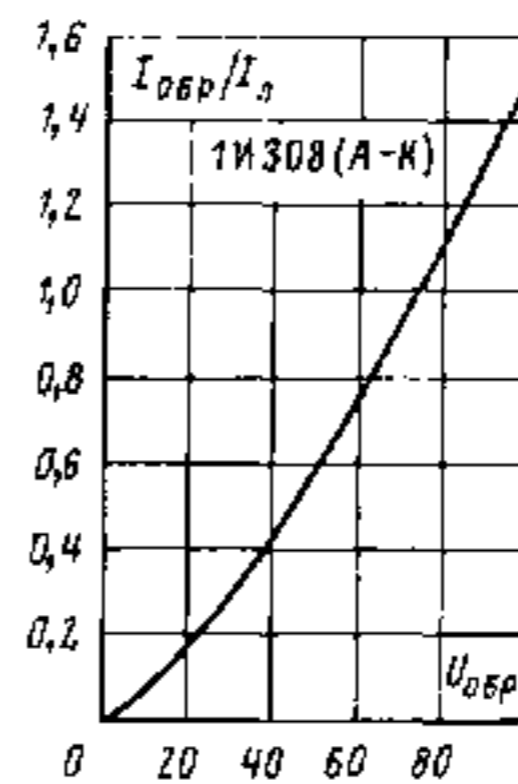
Constant direct current on the second ascending branch of the volt-ampere characteristic at temperature:				
from 213 to 308 K				
	1I308A, 1I308D			6 mA
	1I308B			4 mA
	1I308B, 1I308E, 1I308K			20 mA
	1I308G			15 mA
	1I308Zh			8 mA
	1I308I			40 mA
	at 343 K			
	1I308A			2 mA
	1I308B			7 mA
	1I308G			3 mA
	1I308E			6 mA
	1I308I			15 mA
Pulse direct current on the second ascending branch of the volt-ampere characteristic at temperatures from 213 to 308 K (at a pulse frequency not exceeding 105 Hz):				
	$\tau_i=1 \mu s$	0.1 μs	0.01 μs	0.001 μs
1I308A	12	20	30	50 mA
1I308B	5	6	7	25 mA
1I308B	90	120	150	250 mA
1I308G	30	45	60	100 mA
1I308D	10	12	15	50 mA
1I308E	40	60	90	250 mA
1I308Zh	18	20	30	100 mA
1I308I	75	120	180	300 mA
1I308K	45	60	90	150 mA
Environmental temperature				From 213 to 343 K

Notes:

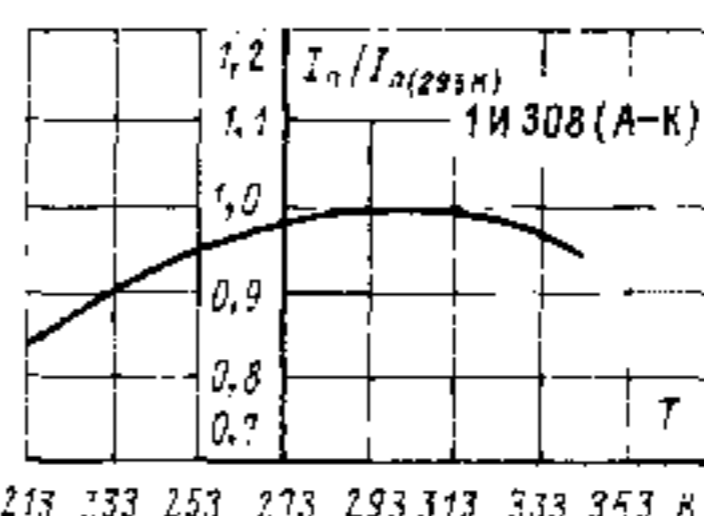
1. DC and pulse reverse current values are 1.5 times higher than the corresponding direct current values.
2. Diodes **1I308B**, **1I308D** at temperatures from 333 to 343 K and **1I308Zh**, **1I308K** at temperatures from 323 to 343 K in static mode should work on the first ascending branch of the volt-ampere characteristic.
3. The pressure force when fastening the diode should not exceed 20 N.
4. Diodes cannot be checked with a tester.



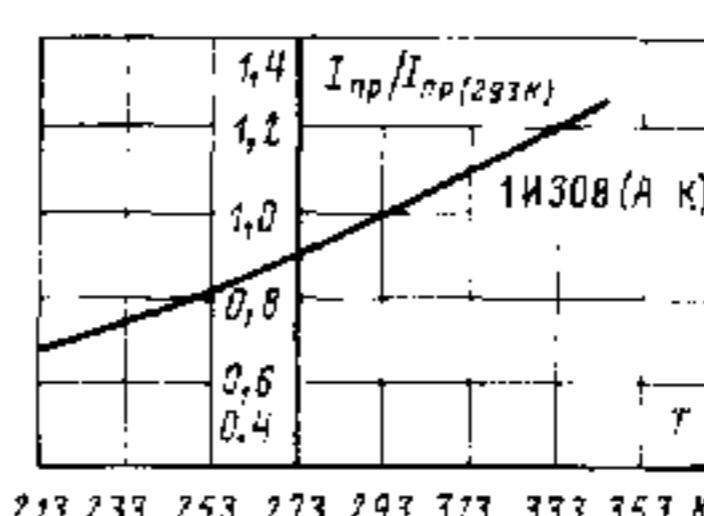
Volt-ampere characteristics.



Inverse branch of the volt-ampere characteristic (voltage is indicated in millivolts).



Dependence of peak current on temperature.



Direct current dependence on temperature.